

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)		
-30	13 at V _{GS} = -10 V	-8	40 nC		
-30	22 at V _{GS} = -4.5 V	°			

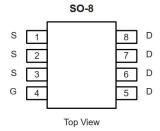
FEATURES

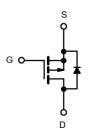
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Adaptor Switch
- Notebook





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 30	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current	T _C = 25 °C	L	- 8		
Continuous Drain Current	T _C = 125 °C	l _D	- 6.1		
Continuous Source Current (Diode Conduction)		Is	- 6.2	A	
Pulsed Drain Current ^a		I _{DM}	- 32		
Single Pulse Avalanche Current	1 0.1 mll	I _{AS}	- 25		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	31	mJ	
Mandanian Danier Display time?	T _C = 25 °C		6.8	W	
Maximum Power Dissipation ^a	T _C = 125 °C	TD	2.3] vv	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient ^{c,d}	PCB Mount ^b	R _{thJA}	85	°C/W	
Junction-to-Foot (Drain)		R_{thJF}	22	- C/W	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. t = 10 s.
- c. Maximum under steady state conditions is 100 $^{\circ}C/W$ d. Based on T $_{C}$ = 25 $^{\circ}C.$



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PARAMETER	SYMBOL	BOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0, I _D =- 250 μA		- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		-1	-	- 2.5	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$, $V_{DS} = -30 V$			-	- 1	μА
		V _{GS} = 0 V, V _{DS} = -30 V, T _J = 125 °C		-	-	- 50	
		$V_{GS} = 0 V, V$	V _{GS} = 0 V, V _{DS} = -30 V, T _J = 175 °C		-	- 150	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -10 \text{ V}, \ V_{DS} \le -5$		- 8	=	1-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} =	- 10 V, I _D = -8 A	-	13	16	
		V _{GS} = - 10 V, I _D = -8 A, T _J = 125 °C		-	-	26	mΩ
		V _{GS} = - 10 V, I _D = -8 A, T _J = 175 °C		-	-	30	
		V _{GS} = - 4.5 V, I _D = -6 A		-	22	25	
Forward Transconductance ^b	9fs	V _{DS} = - 15 V, I _D = - 8 A		-	20	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		0 V V _{DS} = - 15 V, f = 1 MHz	-	2360	-	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		-	260	-	
Reverse Transfer Capacitance	C _{rss}			-	260	-	
Total Gate Charge ^c	Q _q			-	40	-	nC
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -8 \text{ A}$	-	6	-	
Gate-Drain Charge ^c	Q _{gd}			-	10	=	
Gate Resistance	R _g	f = 1 MHz		1-1	6	-	Ω
Turn-On Delay Time ^c	t _{d(on)}	V_{DD} = - 15 V, R_L = 15 Ω $I_D \cong$ - 8 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	10	-	ns
Rise Time ^c	t _r			-	8	-	
Turn-Off Delay Timec	t _{d(off)}			-	42	-	
Fall Time ^c	t _f			-	10	-	
Source-Drain Diode Ratings and Charac	cteristics ^b						
Continous Source-Drain Diode Current	Is	T _C = 25 °C		-	-	- 8	A
Pulse Diode Forward Current	I _{SM}			-	=	- 32	Α.
Body Diode Voltage	VsD	I _S = - 1 A, V _{GS} = 0 V		-	- 0.6	- 1	V
Body Diode Reverse Recovery Time	trr	I _F = -8A, dl/dt = 100 A/μs, T _{.I} = 25 °C		-	12	-	ns
Body Diode Reverse Recovery Charge	Qrr			-	8	-	nC

Notes

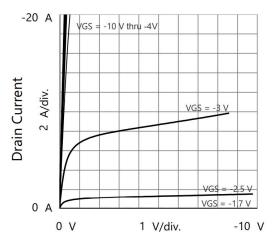
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

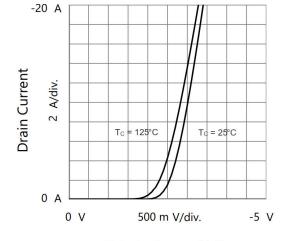
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

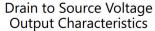


TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)

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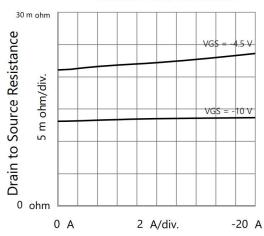




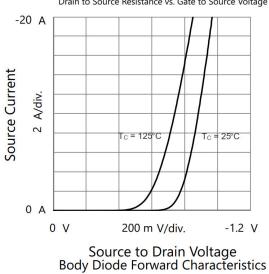


40 m ohm **Drain to Source Resistance** A 8- = al 5 m ohm/div. Tc = 25°C 0 ohm 0 V 1 V/div. -10 V

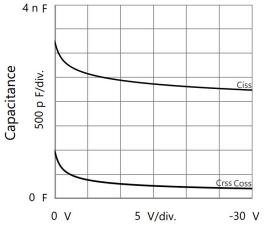
Gate to Source Voltage **Transfer Characteristics**



Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltage



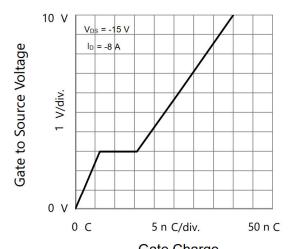
Drain Current Drain to Source Resistance vs. Drain Current



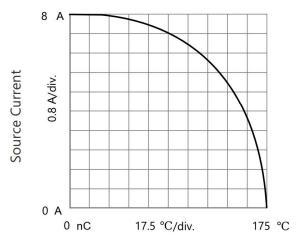
Drain to Source Voltage Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

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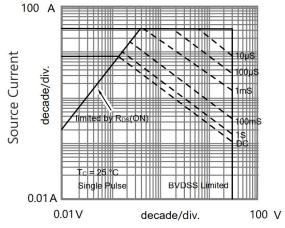


Gate Charge
Gate to Source Voltage vs. GateCharge

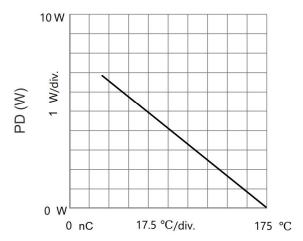


T_C - Case Temperature

Current Derating



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient

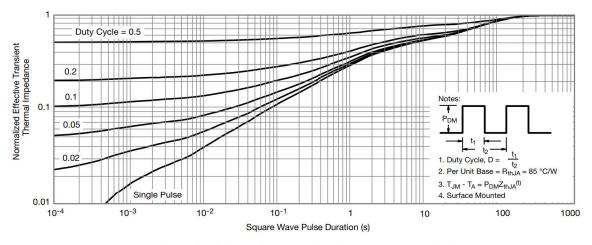


T_C - Case Temperature

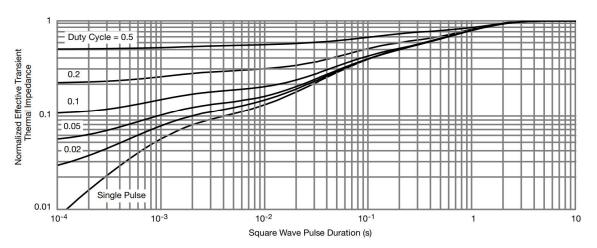
Power Derating

TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)

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Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.





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